

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	3m Ω @10V	120A

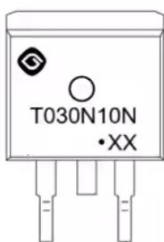
Feature

- Split Gate Trench Technology
- Low $R_{DS(on)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

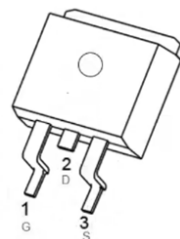
- Power Switching Application

MARKING:

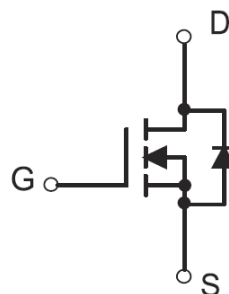


T030N10N = Device Code
XX = Date Code
Solid Dot = Green Indicator

TO-263-2L



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	100	V
Gate - Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	120	A
	$T_C = 100^\circ\text{C}$	I_D	78	A
Pulsed Drain Current ²		I_{DM}	480	A
Single Pulsed Avalanche Current ³		I_{AS}	60	A
Single Pulsed Avalanche Energy ³		E_{AS}	900	mJ
Power Dissipation ⁵		P_D	227	W
$T_C = 25^\circ\text{C}$				
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	62	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	0.55	$^\circ\text{C/W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

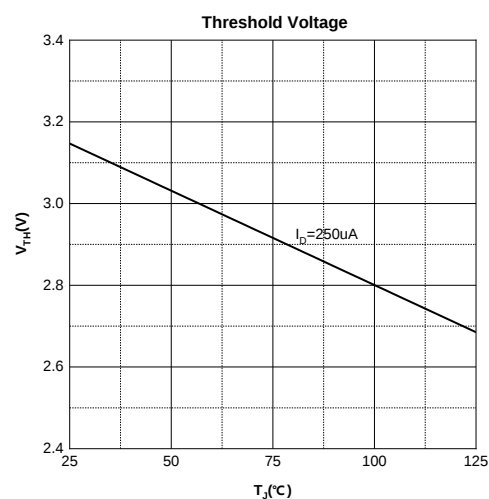
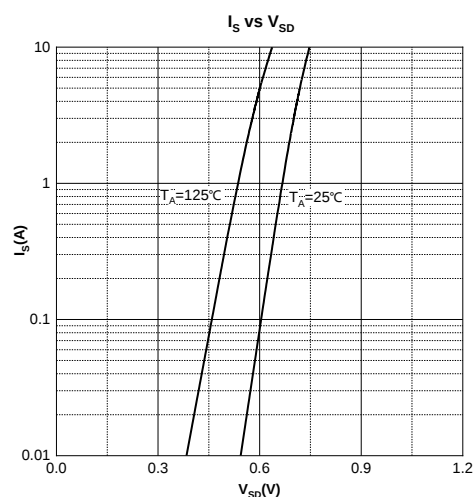
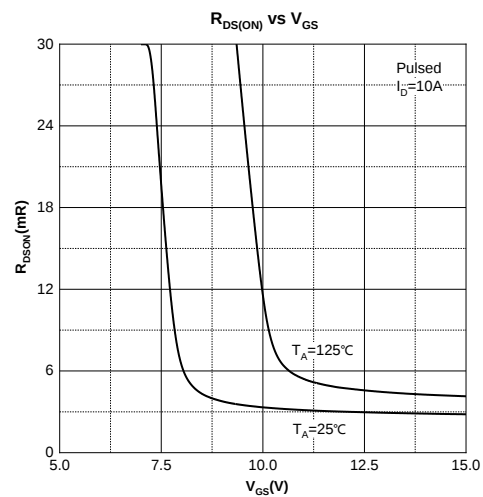
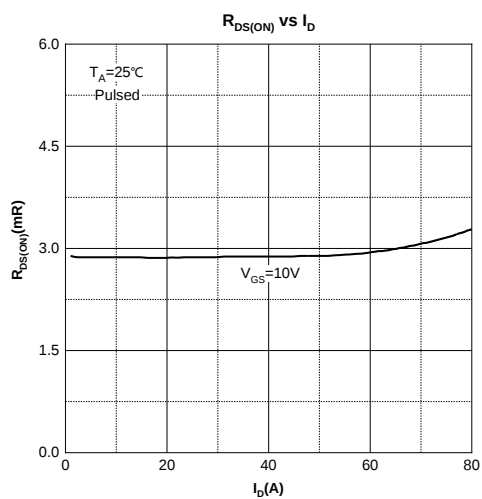
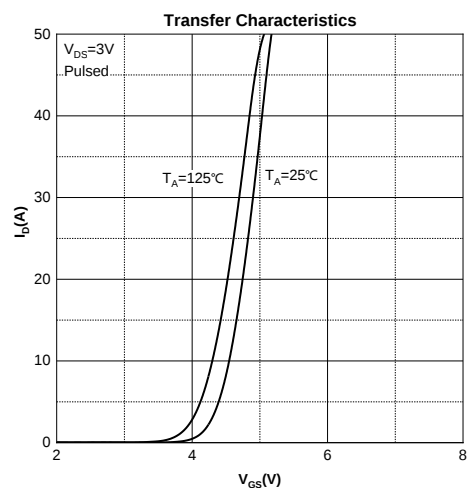
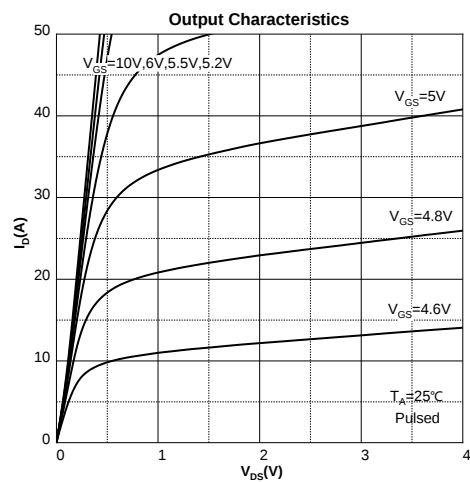
MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

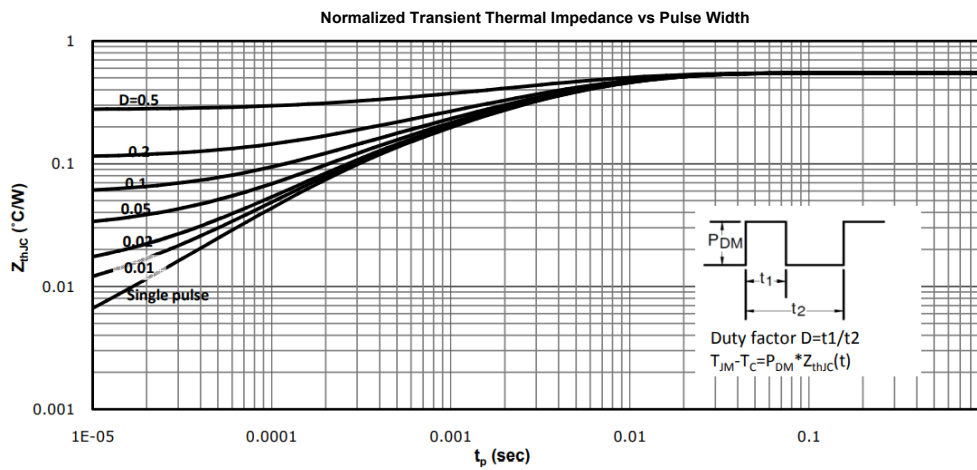
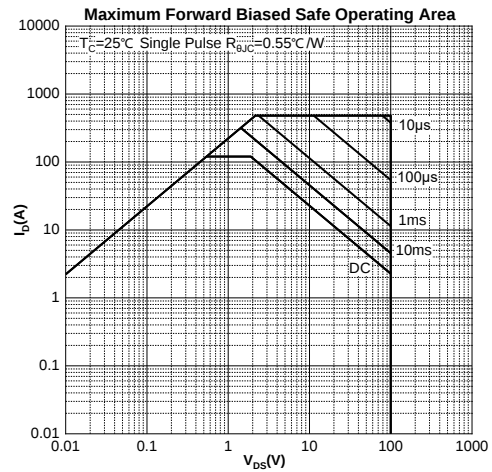
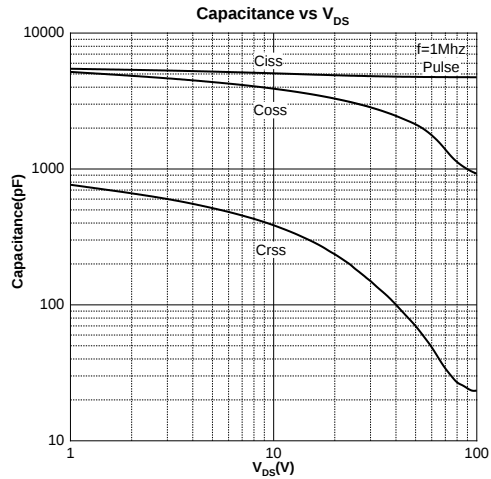
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V			1	μA
Gate - Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ⁴						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	2.6	4	V
Drain-source On-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 20A		3.0	3.9	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 50V, V _{GS} = 0V, f = 0.1MHz		4754		pF
Output Capacitance	C _{oss}			2135		
Reverse Transfer Capacitance	C _{rss}			70		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 0.1MHz		2.6		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 50V, V _{GS} = 10V, I _D = 20A		75		nC
Gate-source Charge	Q _{gs}			22		
Gate-drain Charge	Q _{gd}			19		
Turn-on Delay Time	t _{d(on)}	V _{DD} = 50V, V _{GS} = 10V, I _D = 20A, R _G = 3.3Ω		45		ns
Turn-on Rise Time	t _r			59		
Turn-off Delay Time	t _{d(off)}			70		
Turn-off Fall Time	t _f			31		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	V _{GS} = 0V, I _S = 20A			1.2	V

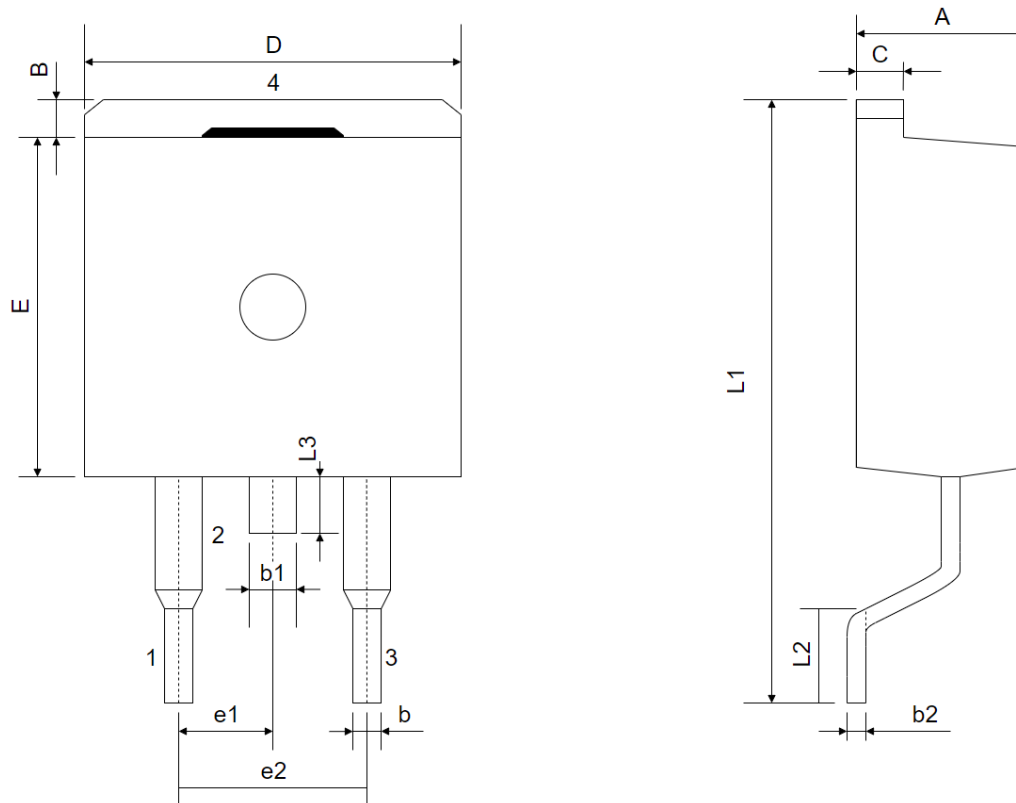
Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.EAS condition: V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.
- 4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 5.The power dissipation P_D is limited by T_{J(MAX)} = 150°C.And device mounted on a large heatsink
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

Typical Characteristics





TO-263-2L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
B	1.000	1.400	0.039	0.055
b	0.700	0.900	0.028	0.035
b1	1.150	1.350	0.045	0.053
b2	0.400	0.600	0.016	0.024
C	1.200	1.400	0.047	0.055
D	9.800	10.200	0.386	0.402
E	9.000	9.400	0.354	0.370
e1	2.340	2.740	0.092	0.108
e2	4.880	5.280	0.192	0.208
L1	15.000	16.000	0.591	0.630
L2	2.240	2.840	0.088	0.112
L3	1.200	1.600	0.047	0.063

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)